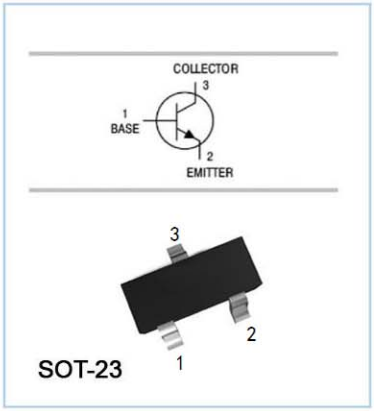
SS8050

NPN Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.



Marking Code: Y1

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	25	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	1.5	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at V_{CE} = 1 V, I_C = 100 mA at V_{CE} = 1 V, I_C = 800 mA	h_{FE}	200	350	-
Collector Base Cutoff Current at V_{CB} = 35 V	I_{CBO}	-	100	nA
Emitter Base Cutoff Current at V_{EB} = 6 V	I_{EBO}	-	100	nA
Collector Base Breakdown Voltage at I_C = 100 µA	$V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at I_C = 2 mA	$V_{(BR)CEO}$	25	-	V
Emitter Base Breakdown Voltage at I_E = 100 µA	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at I_C = 800 mA, I_B = 80 mA	$V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at I_C = 800 mA, I_B = 80 mA	$V_{BE(sat)}$	-	1.2	V
Base Emitter Voltage at V_{CE} = 1 V, I_C = 10 mA	$V_{BE(on)}$	-	1	V
Gain Bandwidth Product at V_{CE} = 10 V, I_C = 50 mA	f_T	120	-	MHz

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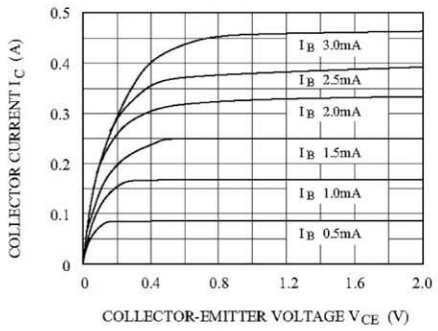
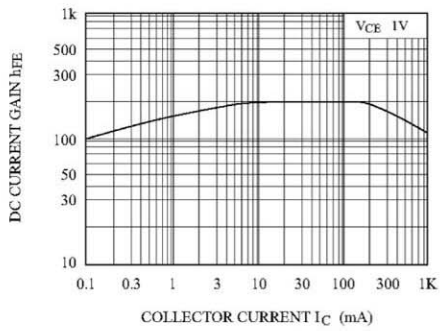
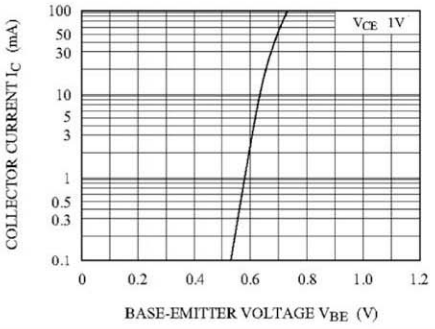
I_C - V_{CE}



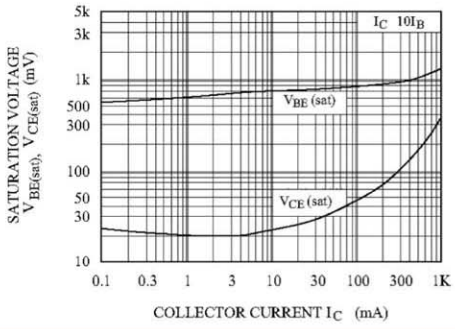
h_{FE} - I_C



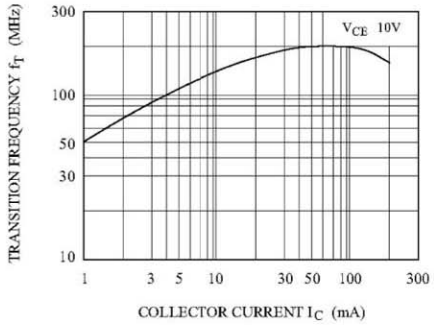
I_C - V_{BE}



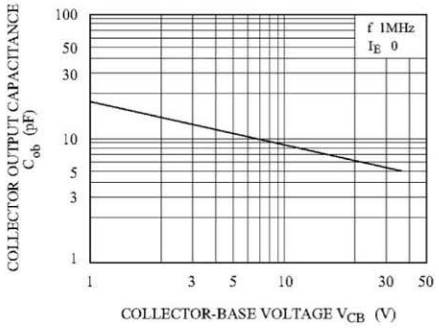
$V_{BE(sat)}$, $V_{CE(sat)}$ - I_C



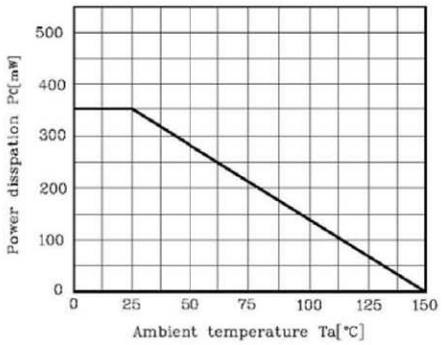
f_T - I_C



C_{ob} - V_{CB}



P_C-T_a



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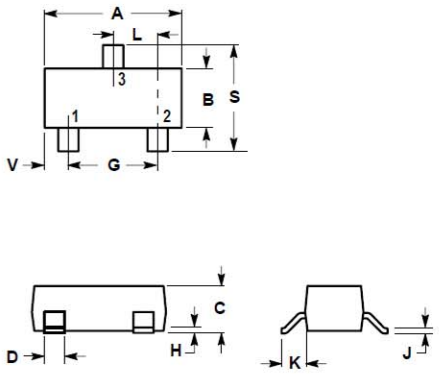
SOT-23 PACKAGE



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

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单击下面可查看定价，库存，交付和生命周期等信息

>>SHIKUES(时科)

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